

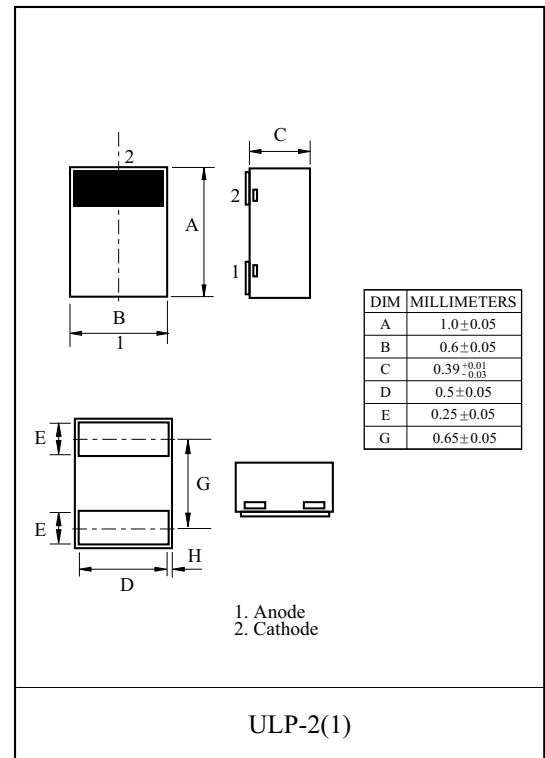
Protection in Portable Electronics Applications.

#### FEATURES

- Transient protection for data lines to  
IEC 61000-4-2(ESD) :  $\pm 20\text{kV}$ (air/contact)  
IEC 61000-4-4(EFT) :  $2.5\text{kV}/50\text{A}$   
IEC 61000-4-5(Surge)  $3\text{A}(t_p=8/20\mu\text{s})$
- Small package for use in portable electronics.
- Suitable replacement for Multi-Layer Varistors in ESD protection applications.  
(\* Multi-Layer Varistors [0402 Size])
- Protects on I/O or power line.
- Low clamping voltage.
- Low leakage current.

#### APPLICATIONS

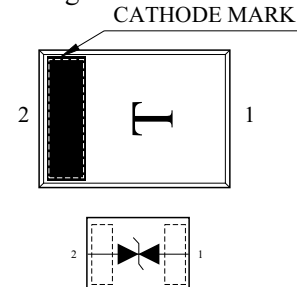
- USB 2.0, 10/100/1000 Ethernet, FireWire, DVI, HDMI, S-ATA
- Mobile Communication
- Consumer Products (STB, MP3, DVD, DSC...)
- LCD-Display, Camera
- Notebooks and desktop computers, peripherals



#### MAXIMUM RATING (Ta=25 °C)

| CHARACTERISTIC                  | SYMBOL           | RATING    | UNIT |
|---------------------------------|------------------|-----------|------|
| Peak Pulse Power (tp=8/20 μs)   | P <sub>PK</sub>  | 63        | W    |
| Peak Pulse Current (tp=8/20 μs) | I <sub>PP</sub>  | 3         | A    |
| Operating Temperature Range     | T <sub>OP</sub>  | -55 ~ 125 | °C   |
| Storage Temperature             | T <sub>stg</sub> | -55 ~ 150 | °C   |

#### Marking



#### ELECTRICAL CHARACTERISTICS (Ta=25 °C)

| CHARACTERISTIC            | SYMBOL           | TEST CONDITION                  | MIN. | TYP. | MAX. | UNIT |
|---------------------------|------------------|---------------------------------|------|------|------|------|
| Reverse Stand-Off Voltage | V <sub>RWM</sub> | -                               | 5.3  | -    | 5.3  | V    |
| Reverse Breakdown Voltage | V <sub>BR</sub>  | I <sub>t</sub> =1mA             | 7    | -    | -    | V    |
| Reverse Leakage Current   | I <sub>R</sub>   | V <sub>RWM</sub> =5.3V          | -    | -    | 100  | nA   |
| Clamping Voltage          | V <sub>C</sub>   | I <sub>PP</sub> =1A, tp=8/20 μs | -    | 11   | -    | V    |
|                           |                  | I <sub>PP</sub> =3A, tp=8/20 μs | -    | 14   | 21   |      |
| Junction Capacitance      | C <sub>J</sub>   | V <sub>R</sub> =0V, f=1MHz      | -    | 0.27 | 0.4  | pF   |